

**A SEMICONDUCTOR DEVICE HAVING A SILICIDED
GATE ELECTRODE AND METHOD OF MANUFACTURE THEREFOR**

ABSTRACT OF THE DISCLOSURE

The present invention provides a semiconductor device, a method of manufacture therefor, and an integrated circuit including the semiconductor device. The semiconductor device (100), among other possible elements, includes a gate oxide (140) located over a substrate (110), and a silicided gate electrode (150) located over the gate oxide (140), wherein the silicided gate electrode (150) includes a first metal and a second metal.